

TO SEPARATE, HOLD TOP AND BOTTOM EDGES, SNAP-APART AND DISCARD CARBON

FORM PTO-892 (REV. 3-78)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		SERIAL NO. 07-702,492	GROUP/ART UNIT 1104	ATTACHMENT TO PAPER NUMBER 17		
NOTICE OF REFERENCES CITED				APPLICANT(S) Inushima et al.				
U.S. PATENT DOCUMENTS								
•		DOCUMENT NO.	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE	
	A							
	B							
	C							
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FOREIGN PATENT DOCUMENTS								
•		DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS	SUB-CLASS	PERTINENT SHTS. DWG. PP. SPEC.
	L	6103539	5-2-86	Japan	Maeda et al.			abstract only
	M				Maeda et al.			abstract only
	N							
	O							
	P							
	Q							
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)								
R	"Modeling of the Plasma-Chemical Synthesis of Silicon Dioxide"; Ivanov et al.; 1985; Khim. Prom-St. (Moscow), (11), 34-5; abstract only							
T	"Properties of Silicon Dioxide Films Prepared From Tetraethoxysilane From Gas and Liquid Phases"; Kedyarskin et al.; 1977; Poluchenie i Analiz Chist. Veshchestv; (2); 40-6; abstract only							
U								
EXAMINER		DATE						
George Goudreau		8-93						
* A copy of this reference is not being furnished with this office action. (See Manual of Patent Examining Procedure, section 707.05 (a).)								

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R	"Silicon Processing For The VLSI Era"; Vol. 2 Process Integration - Wolf; Wolf; Lattice Press; Sunset Beach, Ca; ©1990; pp 110-131, 165-166								
T	"Planarized Deposition of High-Quality Silicon Dioxide Film by Photo-Assisted Plasma CVD at 300 degree C Using Tetraethyl Orthosilicate"; Suzuki et al. Japanese Journal of Appl. Phys., Part 2) 29(12); 1990; pp. 2341-2344								
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